

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

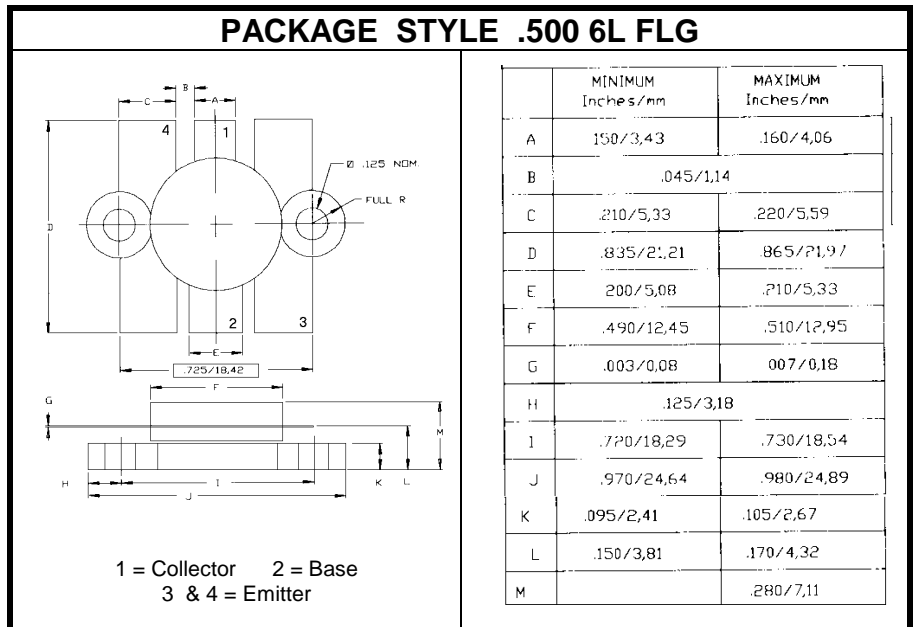
The **ASI 2N6439** is a Common Emitter Device Designed For Large signal output amplifier stages in the 225-400 MHz range.

FEATURES INCLUDE:

- Internal Input Matching Network
- **30:1** Load VSWR Capability
- All Gold Metalization

MAXIMUM RATINGS

V_{CB}	60 V
P_{DISS}	146 W @ T _C = 25 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.2 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 50 mA	33			V
BV_{CES}	I _C = 50 mA	60			V
BV_{CBO}	I _E = 5.0 mA	4.0			V
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	10		100	---
C_{OB}	V _{CB} = 28 V f = 1 MHz		67	75	pF
G_{Pe}	V _{CE} = 28 V P _{OUT} = 60 W f = 225- 400 MHz	7.8	8.5		
G_{Pe}		7.8	10.0		dB
η_C	V _{CE} = 28 V P _{OUT} = 60 W f = 400 MHz	55			%
Ψ		30:1			---